

isc Silicon PNP Power Transistor

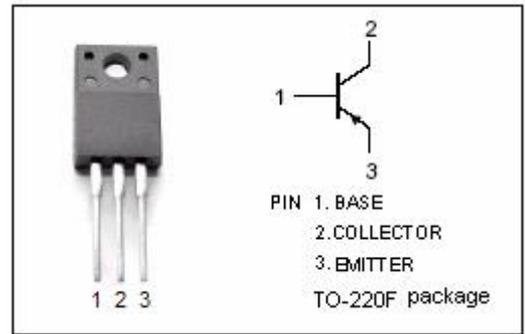
TTA1452B

DESCRIPTION

- High DC current amplifier rate
 $hFE \geq 100 @ V_{CE} = -5V, I_C = -0.5A$
- Low collector-emitter saturation voltage:
 $V_{CE(sat)} \leq -0.4V @ I_C = -6A; I_B = -300mA$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

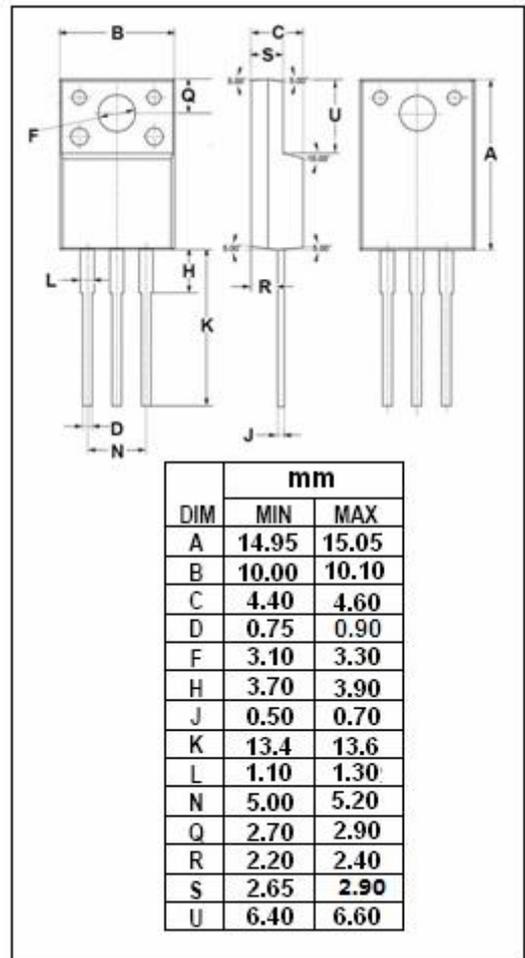
APPLICATIONS

- High current switching



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-12	A
I_{CP}	Collector Current-Pulse	-15	A
P_C	Total Power Dissipation @ $T_a=25^\circ C$	2	W
P_C	Total Power Dissipation @ $T_c=25^\circ C$	30	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon PNP Power Transistor**TTA1452B****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{BR(CEO)}	Collector-Emitter Breakdown voltage	I _C = -50mA; I _B =0	-80			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -6A; I _B = -300mA			-0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -6A; I _B = -300mA			-1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-5	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -80V; I _C = 0			-5	μ A
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -1V	120		240	
h _{FE-2}	DC Current Gain	I _C = -6A; V _{CE} = -1V	40			